



SEMITOP® 2

IGBT module

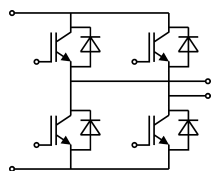
SK 15 GH 066

Features*

- Compact design
- One screw mounting module
- Heat transfer and insulation through direct copper bonded aluminium oxide ceramic (DBC)
- 600V Trench IGBT3 technology
- 600V CAL IHD diode technology
- Integrated NTC temperature sensor
- UL recognized, file no. E 63 532

Typical Applications

- DC/DC Converter
- Motor Drives
- Welding



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Absolute Maximum Ratings				
Symbol	Conditions	Values	Unit	
Inverter - IGBT				
V_{CES}	$T_j = 25\text{ °C}$	600	V	
I_C	$T_j = 175\text{ °C}$	$T_s = 25\text{ °C}$	24	A
		$T_s = 70\text{ °C}$	20	A
I_{Cnom}		15	A	
I_{CRM}		30	A	
V_{GES}		-20 ... 20	V	
t_{psc}	$V_{CC} = 360\text{ V}$ $V_{GE} \leq 15\text{ V}$ $V_{CES} \leq 600\text{ V}$	$T_j = 150\text{ °C}$	6	μs
T_j		-40 ... 175	$^{\circ}\text{C}$	
Inverse - Diode				
V_{RRM}	$T_j = 25\text{ °C}$	600	V	
I_F	$T_j = 175\text{ °C}$	$T_s = 25\text{ °C}$	32	A
		$T_s = 70\text{ °C}$	25	A
I_{FRM}		30	A	
I_{FSM}	10 ms, sin 180°, $T_j = 150\text{ °C}$	95	A	
T_j		-40 ... 175	$^{\circ}\text{C}$	
Module				
$I_{t(RMS)}$	$\Delta T_{terminal}$ at PCB joint = 30 K, per pin	60	A	
T_{stg}		-40 ... 125	$^{\circ}\text{C}$	
V_{isol}	AC, sinusoidal, t = 1 min	2500	V	

Characteristics					
Symbol	Conditions	min.	typ.	max.	Unit
Inverter - IGBT					
$V_{CE(sat)}$	$I_C = 15\text{ A}$ $V_{GE} = 15\text{ V}$ chipelevel	$T_j = 25\text{ °C}$	1.45	1.90	V
		$T_j = 150\text{ °C}$	1.65	2.05	V
V_{CE0}	chipelevel	$T_j = 25\text{ °C}$	0.90	1.00	V
		$T_j = 150\text{ °C}$	0.85	0.90	V
r_{CE}	$V_{GE} = 15\text{ V}$ chipelevel	$T_j = 25\text{ °C}$	37	60	m Ω
		$T_j = 150\text{ °C}$	53	77	m Ω
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 0.21\text{ mA}$	5	5.8	6.5	V
I_{CES}	$V_{GE} = 0\text{ V}, V_{CE} = 600\text{ V}, T_j = 25\text{ °C}$			0.1	mA
C_{ies}	$V_{CE} = 25\text{ V}$ $V_{GE} = 0\text{ V}$	$f = 1\text{ MHz}$	0.86		nF
C_{oes}		$f = 1\text{ MHz}$	0.055		nF
C_{res}		$f = 1\text{ MHz}$	0.024		nF
Q_G	$V_{GE} = -8\text{ V} \dots +15\text{ V}$		100		nC
R_{Gint}	$T_j = 25\text{ °C}$		0		Ω
$t_{d(on)}$	$V_{CC} = 300\text{ V}$	$T_j = 150\text{ °C}$	9		ns
t_r	$I_C = 15\text{ A}$	$T_j = 150\text{ °C}$	9		ns
E_{on}	$R_{Gon} = 6.2\text{ }\Omega$ $R_{Goff} = 6.2\text{ }\Omega$	$T_j = 150\text{ °C}$	0.3		mJ
$t_{d(off)}$	$di/dt_{on} = 1506\text{ A}/\mu\text{s}$	$T_j = 150\text{ °C}$	135		ns
t_f	$di/dt_{off} = 325\text{ A}/\mu\text{s}$	$T_j = 150\text{ °C}$	68		ns
E_{off}	$V_{GE} = +15/-8\text{ V}$	$T_j = 150\text{ °C}$	0.35		mJ
$R_{th(j-s)}$	per IGBT, $\lambda_{paste} = 0.8\text{ W}/(\text{mK})$		2.19		K/W

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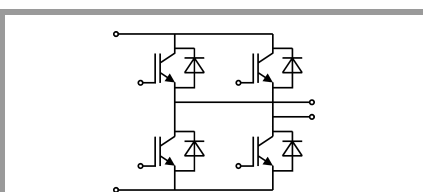
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Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
Inverse - Diode						
$V_F = V_{EC}$	$I_F = 15 \text{ A}$	$T_j = 25 \text{ }^\circ\text{C}$		1.23	1.48	V
	chipelevel	$T_j = 150 \text{ }^\circ\text{C}$		1.15	1.34	V
V_{F0}	chipelevel	$T_j = 25 \text{ }^\circ\text{C}$		0.99	1.10	V
		$T_j = 150 \text{ }^\circ\text{C}$		0.80	0.89	V
r_F	chipelevel	$T_j = 25 \text{ }^\circ\text{C}$		16	26	m Ω
		$T_j = 150 \text{ }^\circ\text{C}$		23	30	m Ω
I_{RRM}	$I_F = 15 \text{ A}$	$T_j = 150 \text{ }^\circ\text{C}$		16		A
Q_{rr}	$di/dt_{off} = 1506 \text{ A}/\mu\text{s}$	$T_j = 150 \text{ }^\circ\text{C}$		1.25		μC
E_{rr}	$V_{GE} = -8 \text{ V}$ $V_{CC} = 300 \text{ V}$	$T_j = 150 \text{ }^\circ\text{C}$		0.26		mJ
$R_{th(j-s)}$	per Diode, $\lambda_{paste}=0.8 \text{ W}/(\text{mK})$			2.7		K/W
Module						
L_{CE}				-		nH
M_s	to heatsink		1.8		2	Nm
W				19		g

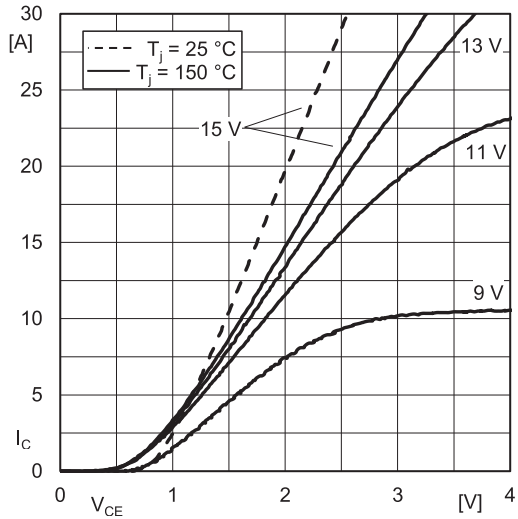


Fig. 1: Typ. IGBT output characteristic, incl. R_{CC+EE}

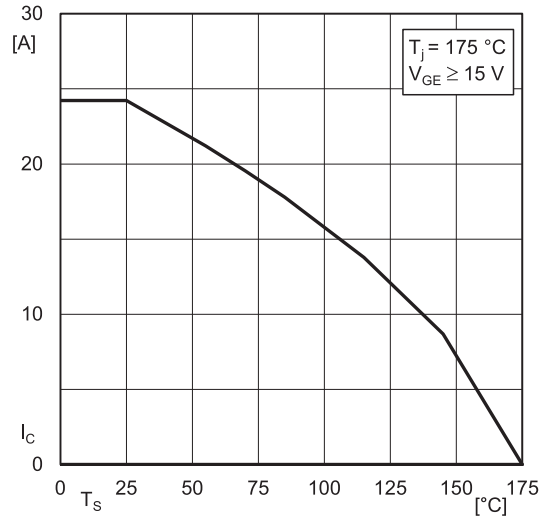


Fig. 2: Rated current vs. temperature $I_C = f(T_S)$

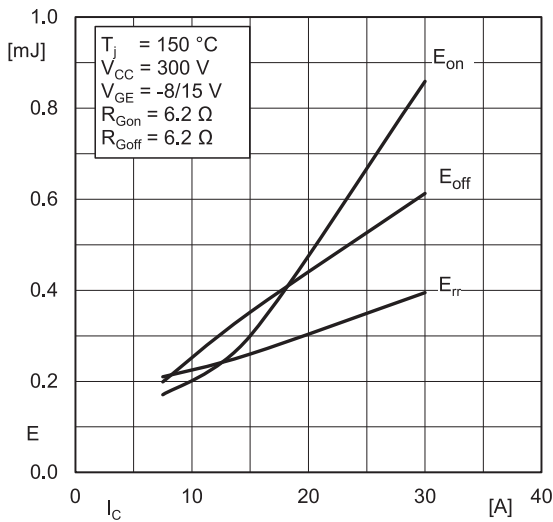


Fig. 3: Typ. turn-on /-off energy = $f(I_C)$

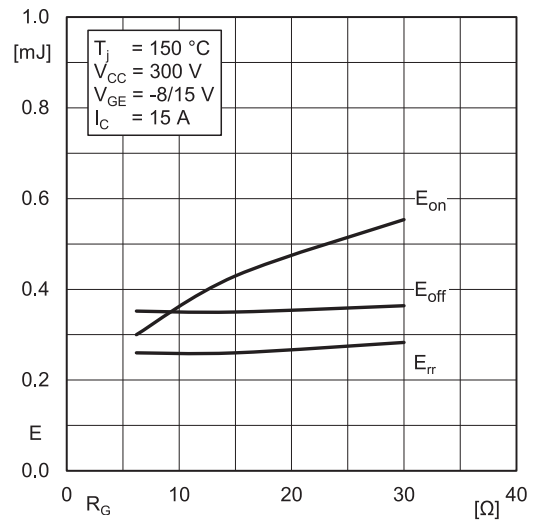


Fig. 4: Typ. turn-on /-off energy = $f(R_G)$

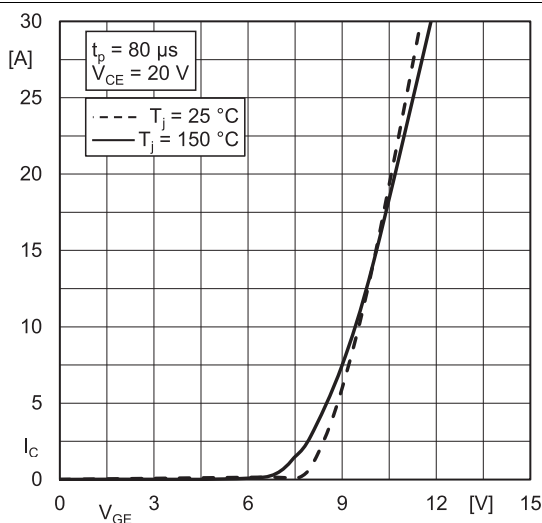


Fig. 5: Typ. IGBT transfer characteristic

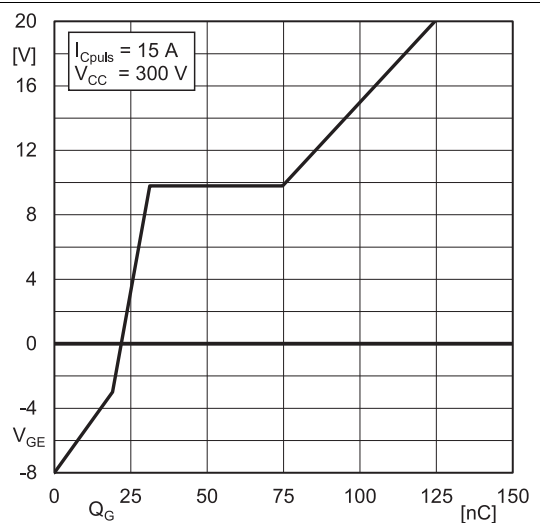


Fig. 6: Typ. IGBT gate charge characteristic

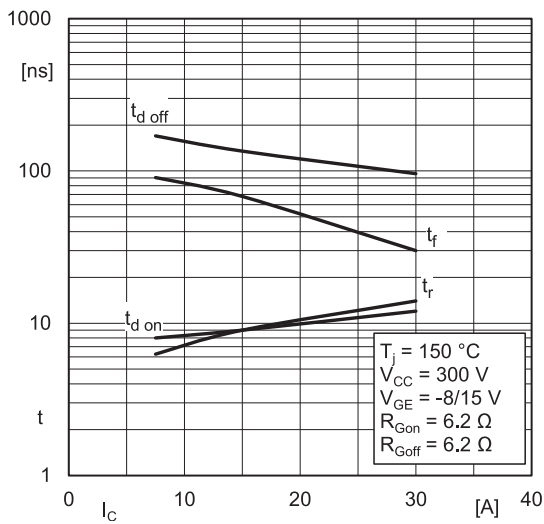


Fig. 7: Typ. switching times = $f(I_C)$

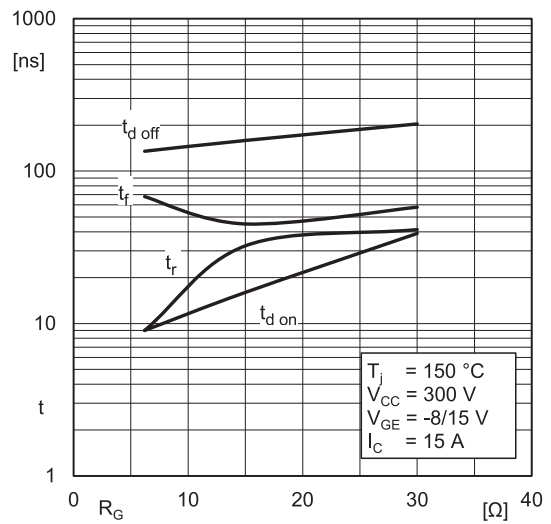


Fig. 8: Typ. switching times = $f(R_G)$

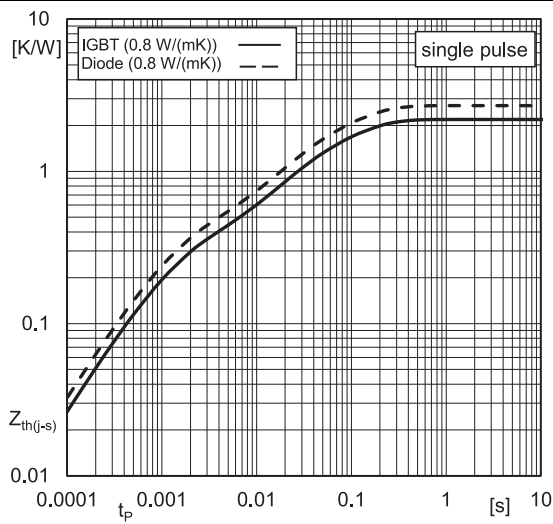


Fig. 9: Typ. transient thermal impedance

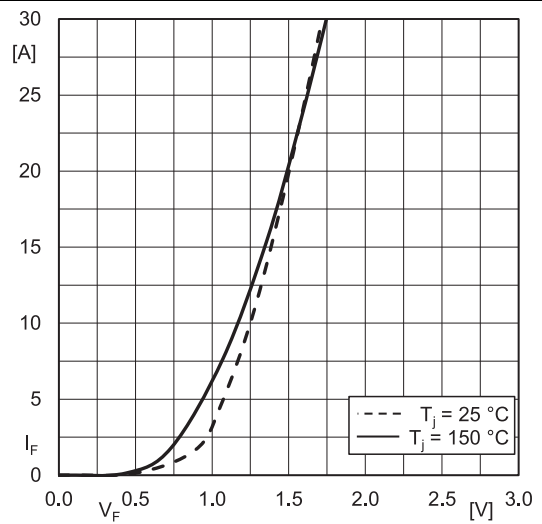


Fig. 10: Typ. Diode forward charact., incl. R_{CC+EE}

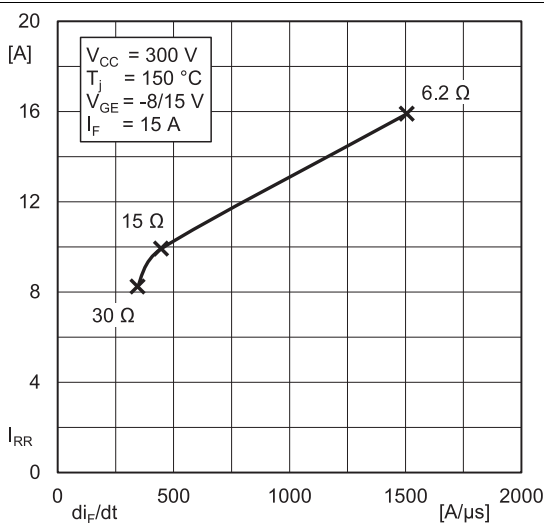


Fig. 11: Typ. Diode peak reverse recovery current

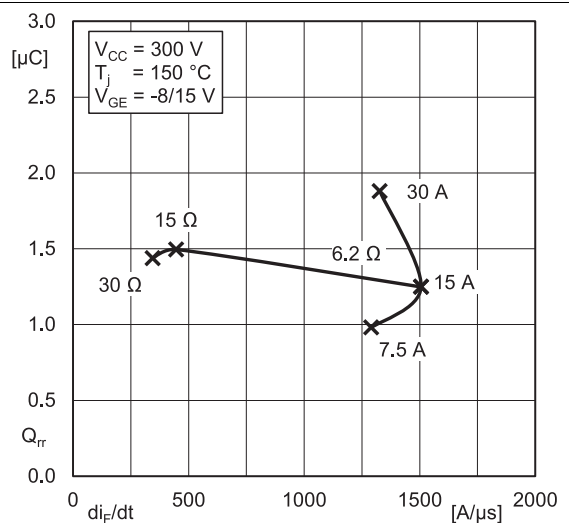
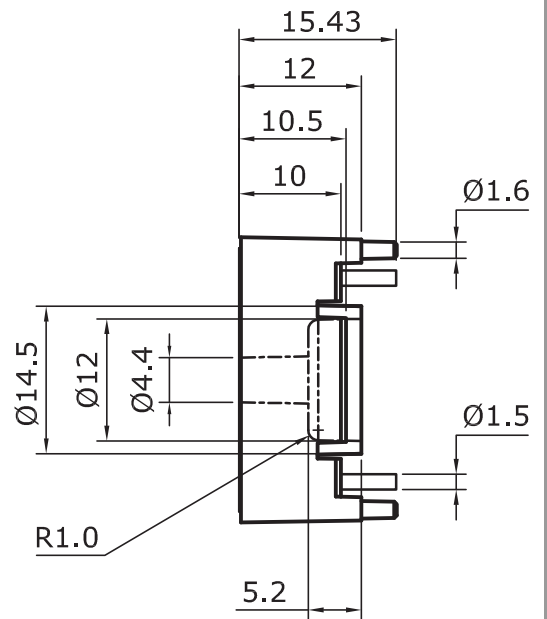
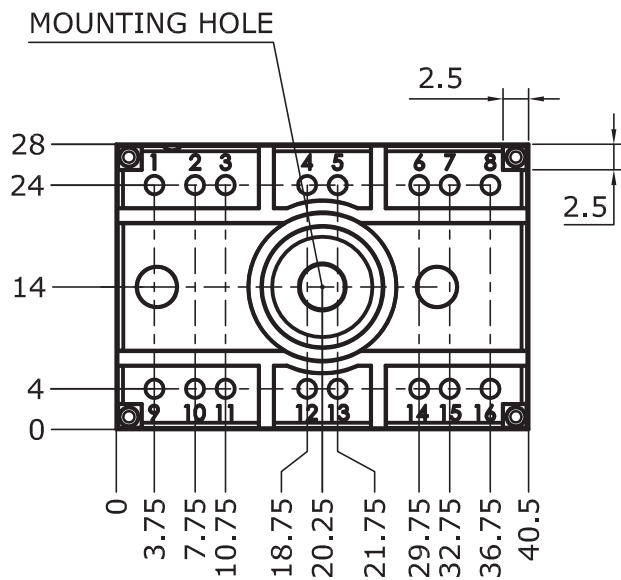
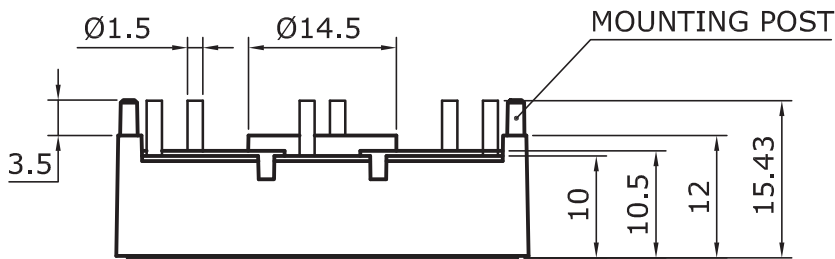


Fig. 12: Typ. Diode reverse recovery charge

Dimensions: mm

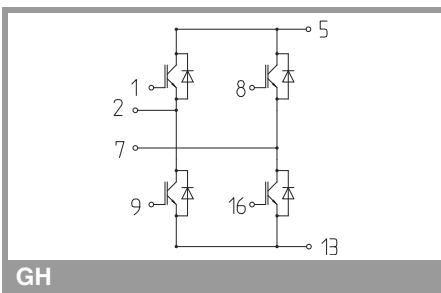
Tolerance system: ISO 2768-m



Suggested hole diameter for solder pins in the circuit board:

- 2.0 mm

SEMITOP®2



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This is an electrostatic discharge sensitive device (ESDS) due to international standard IEC 61340.

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